



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the application of

Katsunori UENO

Serial No.: 10/646,586

Group Art Unit: 2811

Filed: August 22, 2003

Examiner:

For: SILICON CARBIDE n CHANNEL MOS SEMICONDUCTOR
DEVICE AND METHOD FOR MANUFACTURING THE SAME

Certificate of Mailing

I hereby certify that this paper is being deposited with the
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Date: 11-19-03
By: Marc A. Rossi
Marc A. Rossi

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. §1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached Form PTO-1449. Copies of the references listed on Form PTO-1449 are attached.

It is respectfully requested that the information be expressly considered during the prosecution of this application, that these references be made of record therein and appear among the "References Cited" on any patent to issue therefrom, and that an initialed copy of the PTO-1449 be returned to the undersigned.

Respectfully submitted,

Date: 11-19-03

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Attorney Docket No.: FUJI:141A

INFORMATION DISCLOSURE CITATION <small>(Use several sheets if necessary)</small>				Docket Number (Optional) FUJI:141A		Application Number 10/646,586	
				Applicant(s) Katsunori UENO			
				Filing Date August 22, 2003	Group Art Unit 2811		
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILED DATE IF APPROPRIATE
	US	5,776,837	7/98	Palmour	438	767	
	US	5,506,421	4/96	Palmour	257	77	
	US	6,002,143	12/99	Terasawa	257	77	
FOREIGN PATENT DOCUMENTS							
REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
		<p>"Vital Issues for SiC Power Devices"; K. Hara; Materials Science Forum Vols. 264-268 (1998); pgs. 901-906; 1998 Trans Tech Publications, Switzerland</p>					
		<p>"High Voltage Planar 6H-SiC Accufet"; P.M. Shenoy et al.; Materials Science Forum Vols. 264-268 (1998); pgs. 993-996; 1998 Trans Tech Publications, Switzerland</p>					
EXAMINER				DATE CONSIDERED			